

ABSTRACT OF THE DISCLOSURE

- A metal oxide semiconductor transistor includes a semiconductor substrate; a source area formed in a device area of the semiconductor substrate; a drain area formed in the device area; a gate layer formed on and across the device area between the source area and the drain area; a control gate layer; and a diffusion area formed in the device area between the gate area and the control gate area. The control gate layer has a first part including a first end of the control gate layer and a second part including a second end of the control gate layer.
- 5 layer formed on and across the device area between the source area and the drain area; a control gate layer; and a diffusion area formed in the device area between the gate area and the control gate area. The control gate layer has a first part including a first end of the control gate layer and a second part including a second end of the control gate layer.
- 10 The first part is formed on the device area between the source area and the gate layer. The first end is disposed so that there is a gap between the first end and an edge of the device area.